

CM1200HCB-34N

HIGH POWER SWITCHING USE
INSULATED TYPE

Prepared by	K.Kurachi	Revision: A
Date	I.Umezaki	12-Jun-2009

4th-Version HVIGBT (High Voltage Insulated Gate Bipolar Transistor) MODULES

CM1200HCB-34N



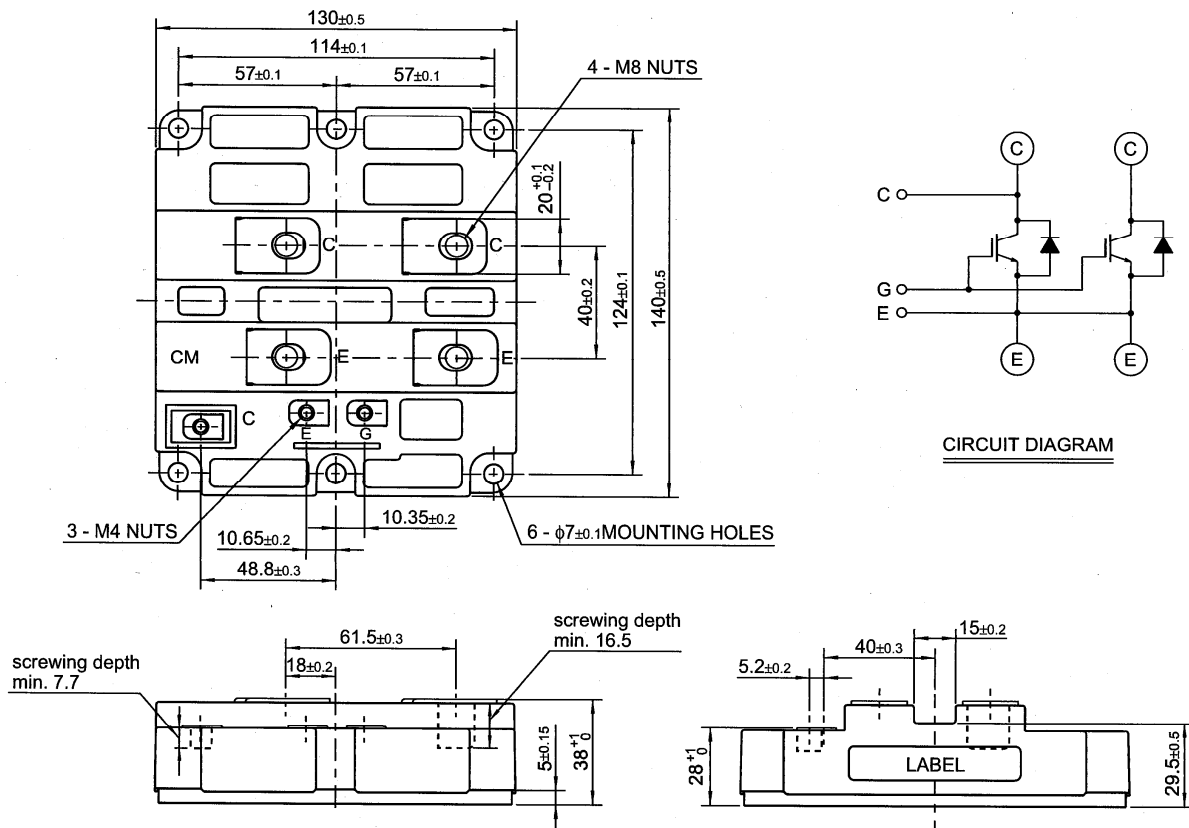
- I_C 1200 A
- V_{CES} 1700 V
- Insulated Type
- 1-element in a Pack
- AlSiC Baseplate
- Trench Gate IGBT : CSTBT™
- Soft Reverse Recovery Diode

APPLICATION

Traction drives, High Reliability Converters / Inverters, DC choppers

OUTLINE DRAWING & CIRCUIT DIAGRAM

Dimensions in mm



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MAXIMUM RATINGS

Symbol	Item	Conditions	Ratings	Unit
V_{CES}	Collector-emitter voltage	$V_{GE} = 0V, T_j = 25^\circ C$	1700	V
V_{GES}	Gate-emitter voltage	$V_{CE} = 0V, T_j = 25^\circ C$	± 20	V
I_C	Collector current	DC, $T_c = 80^\circ C$	1200	A
I_{CM}		Pulse (Note 1)	2400	A
I_E	Emitter current (Note 2)	DC	1200	A
I_{EM}		Pulse (Note 1)	2400	A
P_c	Maximum power dissipation (Note 3)	$T_c = 25^\circ C$, IGBT part	8600	W
V_{iso}	Isolation voltage	RMS, sinusoidal, $f = 60Hz, t = 1min.$	4000	V
T_j	Junction temperature		$-40 \sim +150$	$^\circ C$
T_{op}	Operating temperature		$-40 \sim +125$	$^\circ C$
T_{stg}	Storage temperature		$-40 \sim +125$	$^\circ C$
T_{psc}	Maximum short circuit pulse width	$V_{CC} = 1000V, V_{CE} \leq V_{CES}, V_{GE} = 15V, T_j = 125^\circ C$	10	μs

ELECTRICAL CHARACTERISTICS

Symbol	Item	Conditions	Limits			Unit	
			Min	Typ	Max		
I_{CES}	Collector cutoff current	$V_{CE} = V_{CES}, V_{GE} = 0V$	$T_j = 25^\circ C$	—	—	5	mA
			$T_j = 125^\circ C$	—	4.0	10	
$V_{GE(th)}$	Gate-emitter threshold voltage	$V_{CE} = 10V, I_C = 120mA, T_j = 25^\circ C$	5.5	6.5	7.5	V	
I_{GES}	Gate leakage current	$V_{GE} = V_{GES}, V_{CE} = 0V, T_j = 25^\circ C$	—	—	0.5	μA	
C_{ies}	Input capacitance	$V_{CE} = 10V, V_{GE} = 0V, f = 100kHz$ $T_j = 25^\circ C$	—	220	—	nF	
C_{oes}	Output capacitance		—	12	—	nF	
C_{res}	Reverse transfer capacitance		—	3.5	—	nF	
Q_g	Total gate charge	$V_{CC} = 900V, I_C = 1200A$ $V_{GE} = \pm 15V, T_j = 25^\circ C$	—	15.2	—	μC	
$V_{CE(sat)}$	Collector-emitter saturation voltage	$I_C = 1200A$ (Note 4) $V_{GE} = 15V$	$T_j = 25^\circ C$	—	2.05	2.70	V
			$T_j = 125^\circ C$	—	2.30	—	
$t_{d(on)}$	Turn-on delay time	$V_{CC} = 900V, I_C = 1200A$ $V_{GE} = \pm 15V, R_{G(on)} = 1.1\Omega$	—	—	1.50	μs	
t_r	Turn-on rise time		—	—	0.60	μs	
$E_{on(10\%)}$	Turn-on switching energy (Note 5)	$T_j = 125^\circ C, L_s = 100nH$ Inductive load	—	0.43	—	J/P	
$t_{d(off)}$	Turn-off delay time	$V_{CC} = 900V, I_C = 1200A$ $V_{GE} = \pm 15V, R_{G(off)} = 2.0\Omega$	—	—	3.00	μs	
t_f	Turn-off fall time		—	—	0.60	μs	
$E_{off(10\%)}$	Turn-off switching energy (Note 5)	$T_j = 125^\circ C, L_s = 100nH$ Inductive load	—	0.32	—	J/P	
V_{EC}	Emitter-collector voltage (Note 2)	$I_E = 1200A$ (Note 4) $V_{GE} = 0V$	$T_j = 25^\circ C$	—	2.20	3.00	V
			$T_j = 125^\circ C$	—	1.85	—	
t_{rr}	Reverse recovery time (Note 2)	$V_{CC} = 900V, I_E = 1200A$ $V_{GE} = \pm 15V, R_{G(on)} = 1.1\Omega$	—	—	1.50	μs	
Q_{rr}	Reverse recovery charge (Note 2)		—	410	—	μC	
$E_{rec(10\%)}$	Reverse recovery energy (Note 2),(Note 5)	$T_j = 125^\circ C, L_s = 100nH$ Inductive load	—	0.29	—	J/P	

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THERMAL CHARACTERISTICS

Symbol	Item	Conditions	Limits			Unit
			Min	Typ	Max	
$R_{th(j-c)Q}$	Thermal resistance	Junction to Case, IGBT part	—	—	14.0	K/kW
$R_{th(j-c)R}$	Thermal resistance	Junction to Case, FWDi part	—	—	21.0	K/kW
$R_{th(c-f)}$	Contact thermal resistance	Case to Fin, $\lambda_{grease} = 1W/m^2K$, $D_{(c-f)} = 100 \mu m$	—	10.0	—	K/kW

MECHANICAL CHARACTERISTICS

Symbol	Item	Conditions	Limits			Unit
			Min	Typ	Max	
M_t	Mounting torque	M8: Main terminals screw	7.0	—	13.0	N·m
M_s		M6: Mounting screw	3.0	—	6.0	N·m
M_t		M4: Auxiliary terminals screw	1.0	—	2.0	N·m
m	Mass		—	1.5	—	kg
CTI	Comparative tracking index		600	—	—	—
d_a	Clearance		19.5	—	—	mm
d_s	Creepage distance		32.0	—	—	mm
$L_{P_{CE}}$	Parasitic stray inductance		—	15	—	nH
R_{CC+EE}	Internal lead resistance	$T_c = 25^\circ C$	—	0.21	—	mΩ

- Note 1. Pulse width and repetition rate should be such that junction temperature (T_j) does not exceed T_{opmax} rating (125°C).
 Note 2. The symbols represent characteristics of the anti-parallel, emitter to collector free-wheel diode (FWDi).
 Note 3. Junction temperature (T_j) should not exceed T_{jmax} rating (150°C).
 Note 4. Pulse width and repetition rate should be such as to cause negligible temperature rise.
 Note 5. $E_{on(10\%)} / E_{off(10\%)} / E_{rec(10\%)}$ are the integral of $0.1V_{CE} \times 0.1I_C \times dt$.

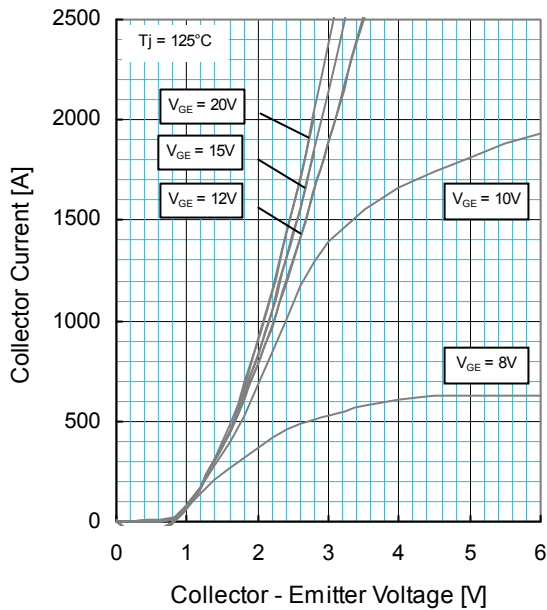
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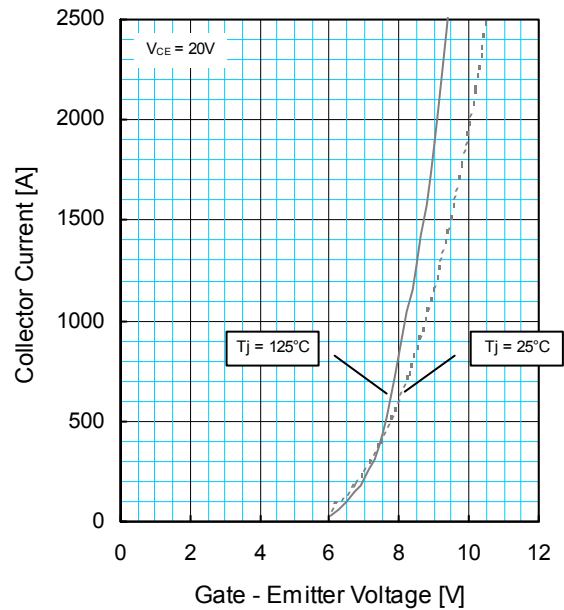
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PERFORMANCE CURVES

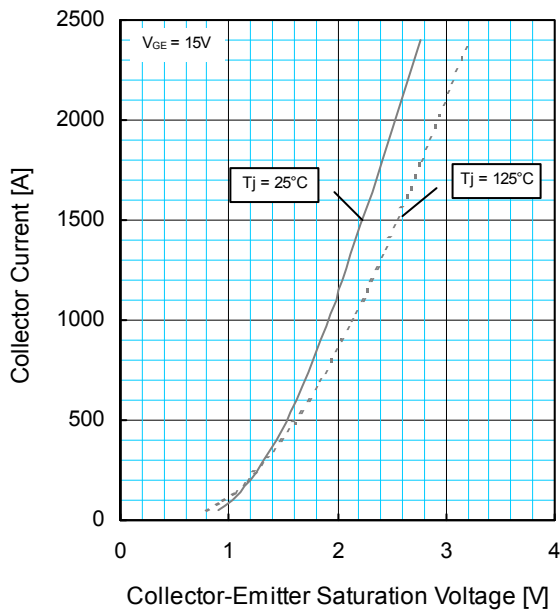
OUTPUT CHARACTERISTICS (TYPICAL)



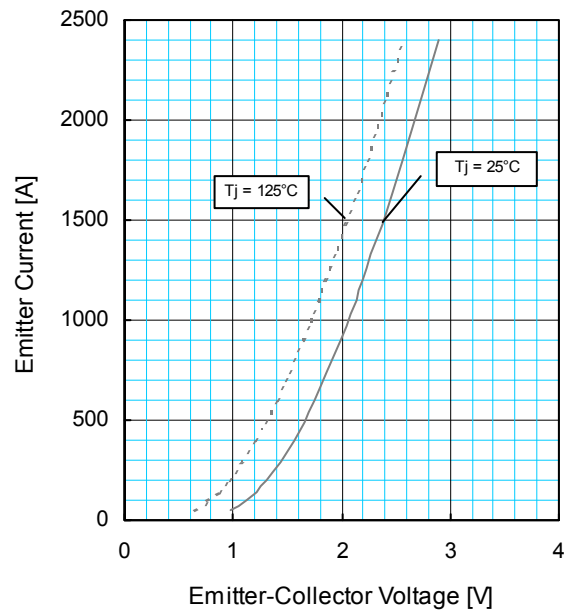
TRANSFER CHARACTERISTICS (TYPICAL)



COLLECTOR-EMITTER SATURATION VOLTAGE CHARACTERISTICS (TYPICAL)



FREE-WHEEL DIODE FORWARD CHARACTERISTICS (TYPICAL)



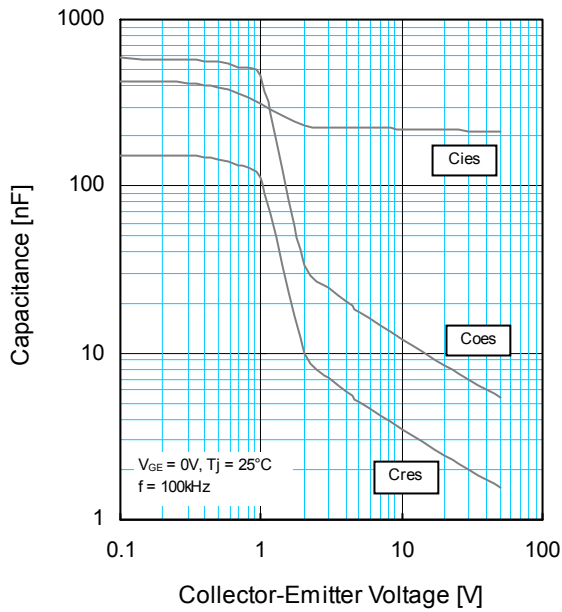
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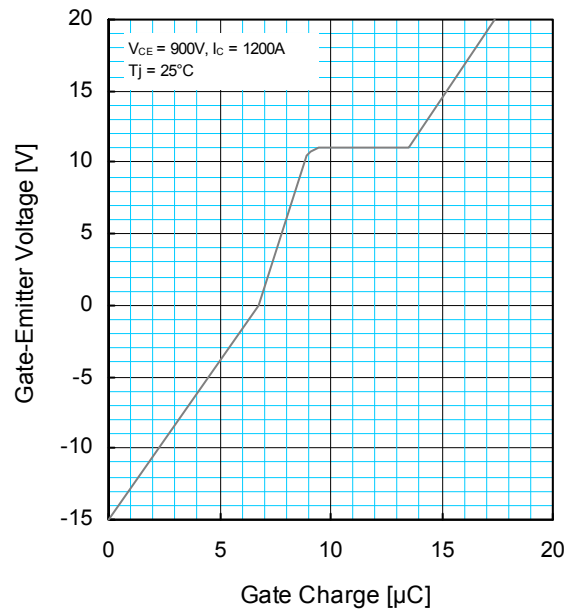
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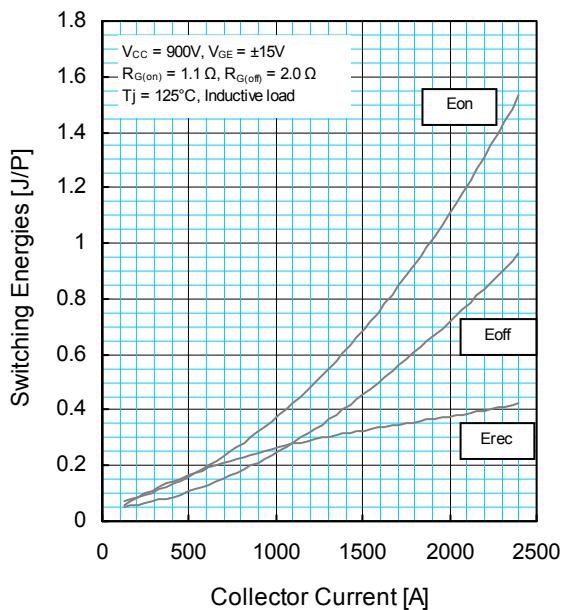
CAPACITANCE CHARACTERISTICS (TYPICAL)



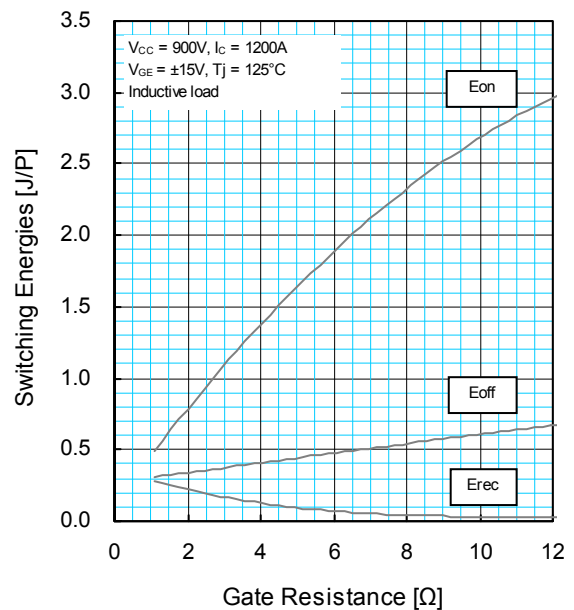
GATE CHARGE CHARACTERISTICS (TYPICAL)



HALF-BRIDGE SWITCHING ENERGY CHARACTERISTICS (TYPICAL)



HALF-BRIDGE SWITCHING ENERGY CHARACTERISTICS (TYPICAL)



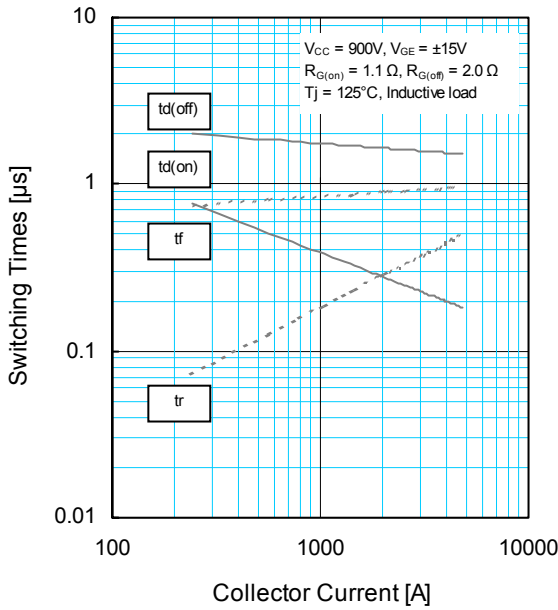
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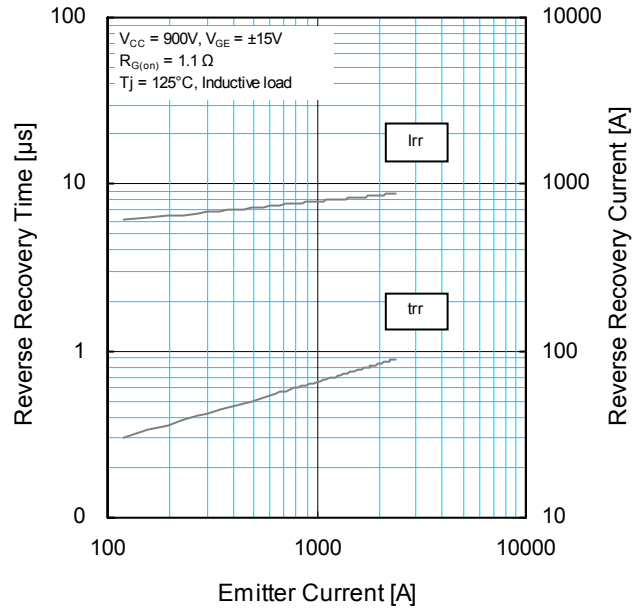
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PERFORMANCE CURVES

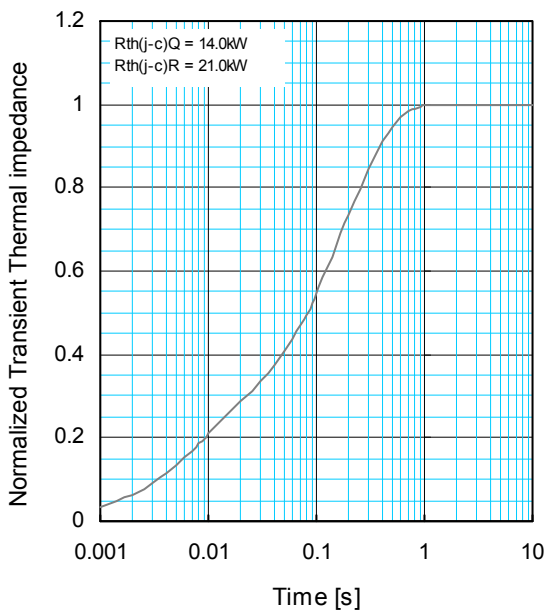
HALF-BRIDGE SWITCHING TIME CHARACTERISTICS (TYPICAL)



FREE-WHEEL DIODE REVERSE RECOVERY CHARACTERISTICS (TYPICAL)



TRANSIENT THERMAL IMPEDANCE CHARACTERISTICS



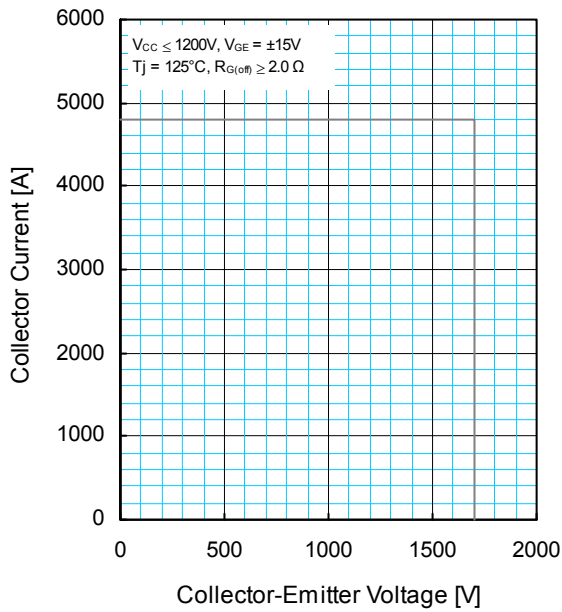
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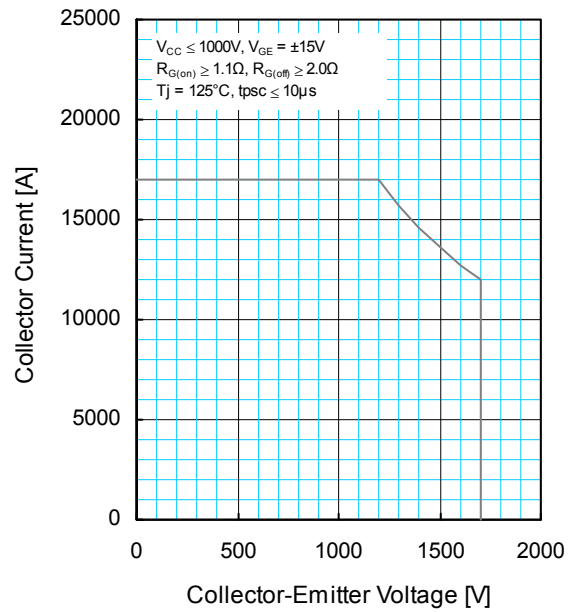
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PERFORMANCE CURVES

REVERSE BIAS SAFE OPERATING AREA (RBSOA)



SHORT CIRCUIT SAFE OPERATING AREA (SCSOA)



FREE-WHEEL DIODE REVERSE RECOVERY SAFE OPERATING AREA (RRSOA)

